



Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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**2N2219
2N2219A**
**SILICON
NPN TRANSISTORS**



TO-39 CASE



www.centralsemi.com

DESCRIPTION:

The CENTRAL SEMICONDUCTOR 2N2219 and 2N2219A are silicon NPN transistors manufactured by the epitaxial planar process, and designed for small signal general purpose and switching applications.

MARKING: FULL PART NUMBER

MAXIMUM RATINGS: ($T_A=25^\circ\text{C}$ unless otherwise noted)

	SYMBOL	2N2219	2N2219A	UNITS
Collector-Base Voltage	V_{CBO}	60	75	V
Collector-Emitter Voltage	V_{CEO}	30	40	V
Emitter-Base Voltage	V_{EBO}	5.0	6.0	V
Continuous Collector Current	I_C	800		mA
Power Dissipation	P_D	800		mW
Power Dissipation ($T_C=25^\circ\text{C}$)	P_D	3.0		W
Operating and Storage Junction Temperature	T_J, T_{stg}	-65 to +200		$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS: ($T_A=25^\circ\text{C}$)

SYMBOL	TEST CONDITIONS	2N2219		2N2219A		UNITS
		MIN	MAX	MIN	MAX	
I_{CBO}	$V_{CB}=50\text{V}$	-	10	-	-	nA
I_{CBO}	$V_{CB}=60\text{V}$	-	-	-	10	nA
I_{CEV}	$V_{CE}=60\text{V}, V_{EB}=3.0\text{V}$	-	-	-	10	nA
I_{EBO}	$V_{EB}=3.0\text{V}$	-	10	-	10	nA
BV_{CBO}	$I_C=10\mu\text{A}$	60	-	75	-	V
BV_{CEO}	$I_C=10\text{mA}$	30	-	40	-	V
BV_{EBO}	$I_E=10\mu\text{A}$	5.0	-	6.0	-	V
$V_{CE(\text{SAT})}$	$I_C=150\text{mA}, I_B=15\text{mA}$	-	0.4	-	0.3	V
$V_{CE(\text{SAT})}$	$I_C=500\text{mA}, I_B=50\text{mA}$	-	1.6	-	1.0	V
$V_{BE(\text{SAT})}$	$I_C=150\text{mA}, I_B=15\text{mA}$	-	1.3	-	1.2	V
$V_{BE(\text{SAT})}$	$I_C=500\text{mA}, I_B=50\text{mA}$	-	2.6	-	2.0	V
h_{FE}	$V_{CE}=10\text{V}, I_C=100\mu\text{A}$	35	-	35	-	
h_{FE}	$V_{CE}=10\text{V}, I_C=1.0\text{mA}$	50	-	50	-	
h_{FE}	$V_{CE}=10\text{V}, I_C=10\text{mA}$	75	-	75	-	
h_{FE}	$V_{CE}=10\text{V}, I_C=150\text{mA}$	100	300	100	300	
h_{FE}	$V_{CE}=1.0\text{V}, I_C=150\text{mA}$	50	-	50	-	
h_{FE}	$V_{CE}=10\text{V}, I_C=500\text{mA}$	30	-	-	-	
h_{FE}	$V_{CE}=10\text{V}, I_C=500\text{mA}$	-	-	40	-	

R1 (31-July 2013)

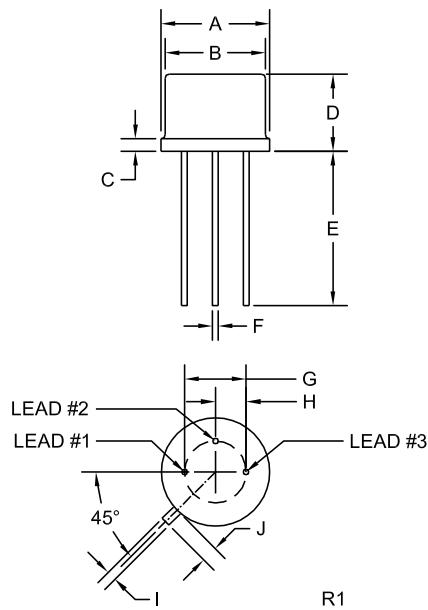
2N2219
2N2219A

SILICON
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ELECTRICAL CHARACTERISTICS - Continued: ($T_A=25^\circ\text{C}$)		2N2219		2N2219A		UNITS
SYMBOL	TEST CONDITIONS	MIN	MAX	MIN	MAX	
f_T	$V_{CE}=20\text{V}$, $I_C=20\text{mA}$	250	-	300	-	MHz
C_{ob}	$V_{CB}=10\text{V}$, $f=100\text{kHz}$	-	8.0	-	8.0	pF
t_{on}	$V_{CC}=30\text{V}$, $I_C=150\text{mA}$, $I_B=15\text{mA}$	-	35	-	35	ns
t_{off}	$V_{CC}=30\text{V}$, $I_C=150\text{mA}$, $I_{B1}=I_{B2}=15\text{mA}$	-	285	-	285	ns

TO-39 CASE - MECHANICAL OUTLINE



SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A (DIA)	0.335	0.370	8.51	9.40
B (DIA)	0.315	0.335	8.00	8.51
C	-	0.040	-	1.02
D	0.240	0.260	6.10	6.60
E	0.500	-	12.70	-
F (DIA)	0.016	0.021	0.41	0.53
G (DIA)	0.200		5.08	
H	0.100		2.54	
I	0.028	0.034	0.71	0.86
J	0.029	0.045	0.74	1.14

TO-39 (REV: R1)

LEAD CODE:

- 1) Emitter
- 2) Base
- 3) Collector

MARKING: FULL PART NUMBER

R1 (31-July 2013)

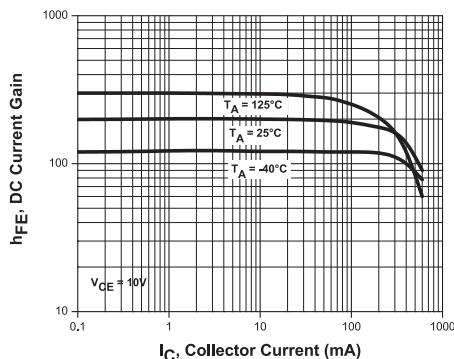
2N2219
2N2219A

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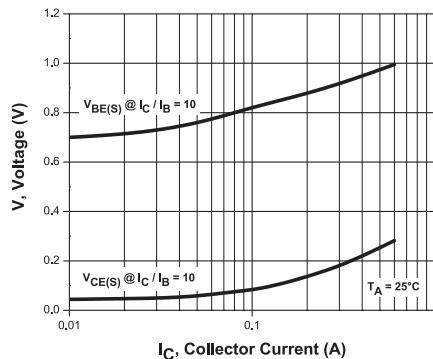
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TYPICAL ELECTRICAL CHARACTERISTICS

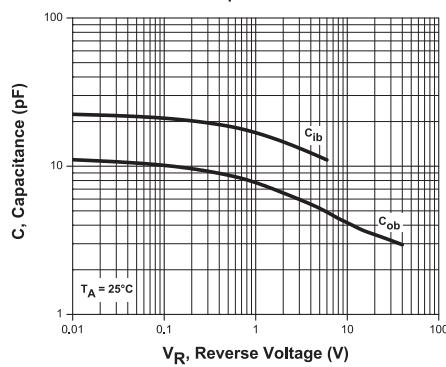
DC Current Gain



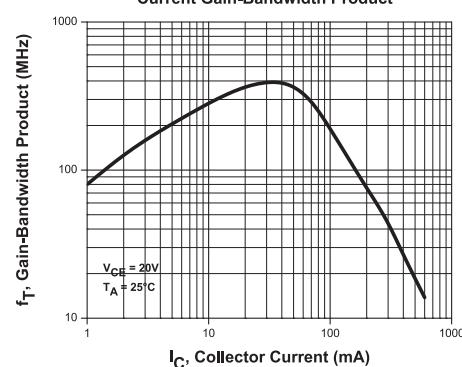
"ON" Voltage



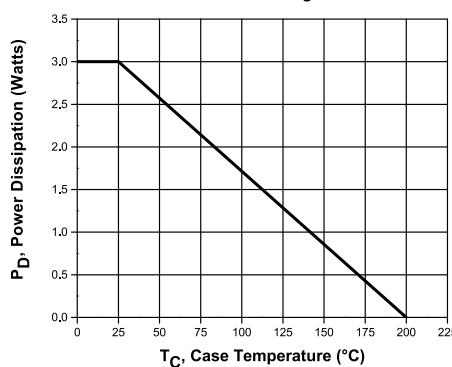
Capacitance



Current Gain-Bandwidth Product



Power Derating



R1 (31-July 2013)

OUTSTANDING SUPPORT AND SUPERIOR SERVICES



PRODUCT SUPPORT

Central's operations team provides the highest level of support to insure product is delivered on-time.

- Supply management (Customer portals)
- Inventory bonding
- Consolidated shipping options
- Custom bar coding for shipments
- Custom product packing

DESIGNER SUPPORT/SERVICES

Central's applications engineering team is ready to discuss your design challenges. Just ask.

- Free quick ship samples (2nd day air)
- Online technical data and parametric search
- SPICE models
- Custom electrical curves
- Environmental regulation compliance
- Customer specific screening
- Up-screening capabilities
- Special wafer diffusions
- PbSn plating options
- Package details
- Application notes
- Application and design sample kits
- Custom product and package development

REQUESTING PRODUCT PLATING

1. If requesting Tin/Lead plated devices, add the suffix " TIN/LEAD" to the part number when ordering (example: 2N2222A TIN/LEAD).
2. If requesting Lead (Pb) Free plated devices, add the suffix " PBFREE" to the part number when ordering (example: 2N2222A PBFREE).

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